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FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO
01/24/2001	Lap-Wai Chow	B-3964 618029-8	4228
7590 07/27/2005		EXAMINER	
LADAS & PARRY		NGUYEN, JOSEPH H	
,	ITE 2100	ART UNIT	PAPER NUMBER
,,		2815	
	01/24/2001 7590 07/27/2005 PARRY	01/24/2001 Lap-Wai Chow 7590 07/27/2005 PARRY HIRE BOULEVARD, SUITE 2100	01/24/2001 Lap-Wai Chow B-3964 618029-8 7590 07/27/2005 EXAM PARRY HIRE BOULEVARD, SUITE 2100 LES, CA 90036-5679 ART UNIT

DATE MAILED: 07/27/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

<u> </u>	Application No.	Applicant(s)		
	09/768,904	CHOW ET AL.		
Office Action Summary	Examiner	Art Unit		
	Joseph Nguyen	2815		
The MAILING DATE of this communication appears on the cover sheet with the correspondence address				
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply - If NO period for reply is specified above, the maximum statutory period was a failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply be time within the statutory minimum of thirty (30) day will apply and will expire SIX (6) MONTHS from a cause the application to become ABANDONE	nely filed s will be considered timely. the mailing date of this communication. D (35 U.S.C. § 133).		
Status				
 1) Responsive to communication(s) filed on 25 M 2a) This action is FINAL. 2b) This 3) Since this application is in condition for alloward closed in accordance with the practice under E 	action is non-final. nce except for formal matters, pro			
Disposition of Claims				
 4) Claim(s) 1-20,23 and 24 is/are pending in the at 4a) Of the above claim(s) is/are withdraw 5) Claim(s) is/are allowed. 6) Claim(s) 1-20,23 and 24 is/are rejected. 7) Claim(s) is/are objected to. 8) Claim(s) are subject to restriction and/or 	wn from consideration.			
Application Papers	•			
9) ☐ The specification is objected to by the Examine 10) ☑ The drawing(s) filed on <u>07 May 2001</u> is/are: a) Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct 11) ☐ The oath or declaration is objected to by the Examine	☑ accepted or b)☐ objected to drawing(s) be held in abeyance. Section is required if the drawing(s) is ob	e 37 CFR 1.85(a). jected to. See 37 CFR 1.121(d).		
Priority under 35 U.S.C. § 119				
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority documents 2. Certified copies of the priority documents 3. Copies of the certified copies of the priority documents application from the International Bureau * See the attached detailed Office action for a list	s have been received. s have been received in Applicati rity documents have been receive u (PCT Rule 17.2(a)).	on No ed in this National Stage		
Attachment(s) 1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date 5/2/05.	4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal F 6) Other:	•		

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DETAILED ACTION

Claim Rejections - 35 USC § 102

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 1-3, 5-7, 9-11, 13-15, 17-20 and 23-24 are rejected under 35 U.S.C. 102(b) as being anticipated by Sun et al. (US 5,345,105).

Regarding claim 1, Sun et al. discloses on figure 6 a semiconducting device adapted to prevent and/or to thwart reverse engineering comprising a field oxide layer (cross sectional shaped layer between substrate 12 and dielectric 14) disposed on a semiconductor substrate 12 ((col. 2, lines 56-57) and within a contact region (left side portion of device 10 is herein considered "contact region"); a metal plug contact (conductive layer between metal 16 and field oxide) disposed within said contact region and above said field oxide layer, wherein said metal plug contact contacts said field oxide layer, and wherein said field oxide layer electrically isolates said metal plug contact from said contact region; and a metal 16 (col. 3, lines 22-23) connected to said metal plug contact.

Note that although Sun et al. does not teach reverse engineering prevention, the structure shown in figure 6 of Sun et al. shows all the claimed features defined in claim 1, and therefore claim 1 is anticipated. Further, it has been held that the recitation that an element is "adapted to" perform a function is not a positive limitation but only requires the ability to so perform. Thus, it does not constitute a limitation in any patentable sense. In re Hutchinson, 69 USPQ 138.

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Regarding claim 2, Sun et al. discloses the semiconducting device comprises integrated circuits (col. 6, lines 37-38).

Regarding claim 3, it is inherent that the field oxide layer comprises silicon oxide.

Regarding claims 5-7, similar to rejection of claims 1-3 above, Sun et al. discloses on figure 6 all steps of the method set forth in the claimed invention.

Regarding claim 9, Sun et al. discloses on figure 6 a semiconducting device adapted to prevent and/or thwart reverse engineering comprising a field oxide layer (cross sectional shaped layer between substrate 12 and dielectric 14) disposed on a semiconductor substrate 12 adjacent a contact region (right side portion of device 10 is herein considered "contact region"); a metal plug contact (conductive layer between metal 16 and field oxide) having a first surface and a second surface opposite said first surface, said metal plug contact disposed outside said contact region, wherein said second surface of said metal plug contact is disposed above said filed oxide layer and in contact with a dielectric material (field oxide is dielectric material), wherein said metal plug contact is electrically isolated from said contact region; and a metal 16 connected to said first surface of said metal plug contact.

Regarding claim 10, Sun et al. discloses the semiconducting device comprises integrated circuits (col. 6, lines 37-38).

Regarding claim 11, it is inherent that the field oxide layer comprises silicon oxide.

Regarding claims 13-15, similar to rejection of claims 9-11 above, Sun et al. discloses on figure 6 all steps of the method set forth in the claimed invention.

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Regarding claims 17 and 19, Sun et al. discloses on figure 6 the field oxide layer has an uppermost side, said metal plug contact being disposed on said uppermost side of the field oxide layer.

Regarding claims 18 and 20, similar to rejections of claims 17 and 19, Sun et al. discloses all steps of the method set forth in the claimed invention.

Regarding claims 23-24, Sun et al. discloses on figure 6 the filed oxide layer comprises the dielectric material.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 4, 8, 12 and 16 are rejected under 35 U.S.C. 103(a) as being unpatentable over Sun et al., and further in view of Liu et al.

Regarding claims 4, 8, 12 and 16, Sun et al. discloses on figure 6 substantially all structures and/or steps of the method set forth in the claimed invention except the integrated circuits comprising complementary metal oxide semiconductor integrated circuits. However, Liu et al. teaches the integrated circuits comprising complementary metal oxide semiconductor integrated circuits (col. 1, lines 20-21). In view of such teaching, it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify Sun et al. by having the integrated circuits comprising

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complementary metal oxide semiconductor integrated circuits to provide low voltage, low power consumption for digital applications (col. 1, lines 21-22).

Response to Arguments

Applicant's arguments with respect to claims 1-20 and 23-24 have been considered but are most in view of the new ground(s) of rejection.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Joseph Nguyen whose telephone number is (571) 272-1734. The examiner can normally be reached on Monday-Friday, 7:30 am- 4:30 pm. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Tom Thomas can be reached on (571) 272-1664. The fax phone number for the organization where this application or proceeding is assigned is (571) 273-8300 for regular communications.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

JN July 12, 2005

TOM THOMAS
SUPERVISORY PATENT EXAMINER